

ABSTRACT OF THE DISCLOSURE

Overcoating compositions for photoresist and methods for reducing linewidth of the photoresist patterns are disclosed. More specifically, an overcoating composition containing acids is coated on a whole surface of a photoresist pattern
5 formed by a common lithography process to diffuse the acids into the photoresist pattern. The photoresist in the portion where the acids are diffused is developed with an alkali solution to be removed. As a result, the linewidth of positive photoresist patterns can be reduced, and the linewidth of negative photoresist patterns can be prevented from slimming in a subsequent linewidth measurement process using SEM.